/ Descri o pti o ons

TO-220F PNP Silicon PNP transistor in a TO-220F Plastic Package.

/ Features

KTC4511

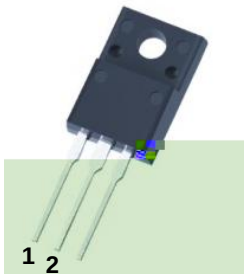
Complementary to KTC4511.

/ Applications

High Power amplifier application.

/ Equivalent oCircuit

/ Pi o nni o ng



PIN1 Base PIN 2 Collector or Emitter

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	R	O
h_{FE} Ra	55 110 80	160

/ Absolute Maximum Ratings(Ta=25)

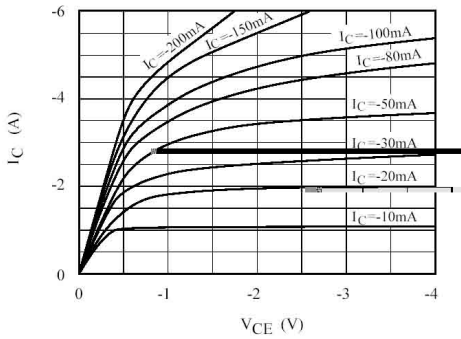
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-6.0	A
Base Current	I_B	-3.0	A
Collector Power Dissipation	P_c(Tc=25)	30	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

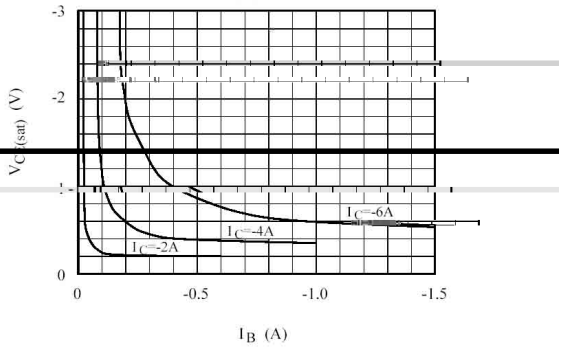
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-25mA I_B=0	-80			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-80V I_E=0			-10	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-6.0V I_C=0			-10	μA
DC Current Gain	h_{FE}	V_{CE}=-4.0V I_C=-2.0A	55		160	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-2.0A I_B=-0.2A			-0.5	V
Transition Frequency	f_T	V_{CE}=-12V I_C=-0.5A		20		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=1.0MHz		150		pF

/ Electrical Characteristic Curve

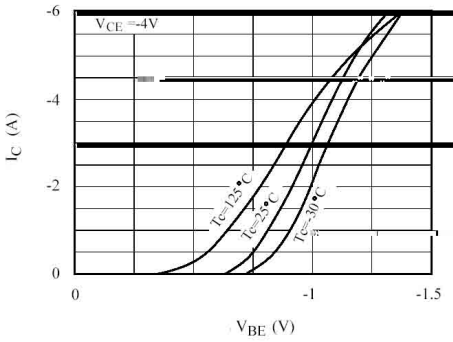
I_C - V_{CE}



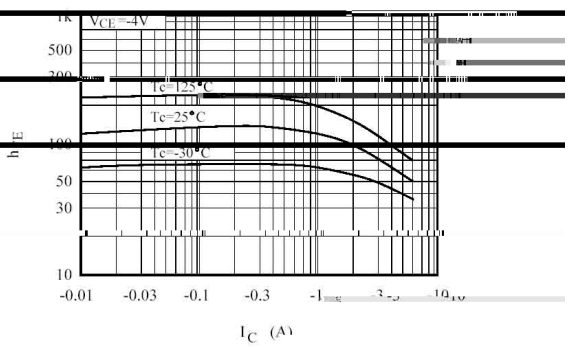
$V_{CE(sat)}$ - I_B



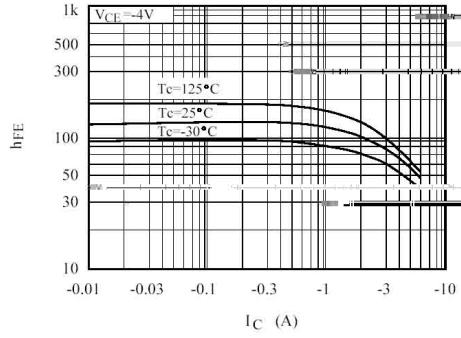
I_C - V_{BE}



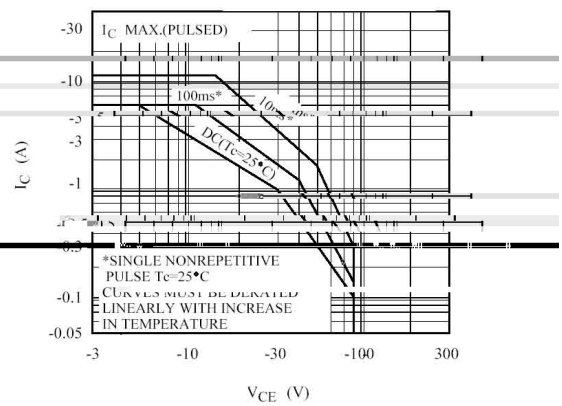
h_{FE} - I_C



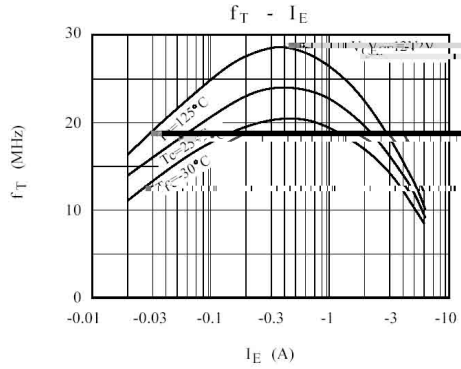
h_{FE} - I_C



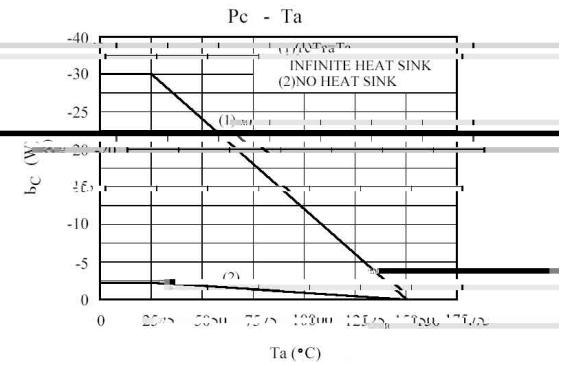
I_C - V_{CE}



f_T - I_E



Pc - Ta



/ Package Dimensions